

PROCESS CHAMBER AND SEMICONDUCTOR PROCESS APPARATUS

ABSTRACT

The present disclosure provides a process chamber and a semiconductor process apparatus. The process chamber is applied in the semiconductor process apparatus and includes a chamber body, a base, and a chuck assembly. The reaction chamber is formed in the chamber body. The base is located in the reaction chamber. The chuck assembly is connected to the base and configured to carry a wafer. The base includes a base body and a plurality of cantilevers. The plurality of cantilevers are arranged evenly along the circumference of the base body. Each cantilever is connected to the inner wall of the chamber body and the outer wall of the base body. The chamber body, the base body, and the cantilever have an integral structure and are made of a material having the electrical conductivity and the thermal conductivity. In the present disclosure, the uniformity of the RF circuit and the uniformity of the overall temperature of the process chamber can be greatly improved. Thus, the yield of the wafer can be greatly improved.

(FIG.1)